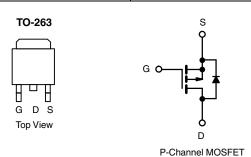


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Vishay Siliconix

# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0070			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = - 4.5 V	0.0110			
I <sub>D</sub> (A)	- 50			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>q</sub> and UIS Tested
- AEC-Q101 Qualifiedd
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



FREE

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM50P03-07-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	- 30	V	
Gate-Source Voltage	$V_{GS}$	± 20	V		
Continuous Drain Currenta	T <sub>C</sub> = 25 °C	I <sub>D</sub>	- 50		
Continuous Drain Current	T <sub>C</sub> = 125 °C		- 50		
Continuous Source Current (Diode Conduct	I <sub>S</sub>	- 50	А		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 200			
Single Pulse Avalanche Current	gle Pulse Avalanche Current		- 50		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Maximum Dawar Dissinationh	T <sub>C</sub> = 25 °C	D	150	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	50	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1	- C/VV	

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 30	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	- 2.0	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 175 °C	-	-	- 250	•	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	V <sub>DS</sub> ≤ - 5 V	- 120	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A	-	0.0050	0.0070		
Due in Course On Chata Basistanas		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A, T <sub>J</sub> = 125 °C	-	-	0.0102	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 30 A, T <sub>J</sub> = 175 °C	-	-	0.0118		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 20 A	-	0.0089	0.0110		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 30 A		-	62	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>GS</sub> = 0 V V <sub>DS</sub> = - 25 V, f = 1 MHz		4304	5380	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$			764	955		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	680	850		
Total Gate Charge <sup>c</sup>	Qg			-	103.5	155		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -75 \text{ A}$	-	14.3	-	nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	26.9	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.4	2.85	4.3	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	17		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 0.2 $\Omega$ $I_D$ $\cong$ - 75 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		-	10	15	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	63	95		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	26	39		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 200	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = - 45 A, V <sub>GS</sub> = 0 V		-	- 0.9	- 1.5	V	

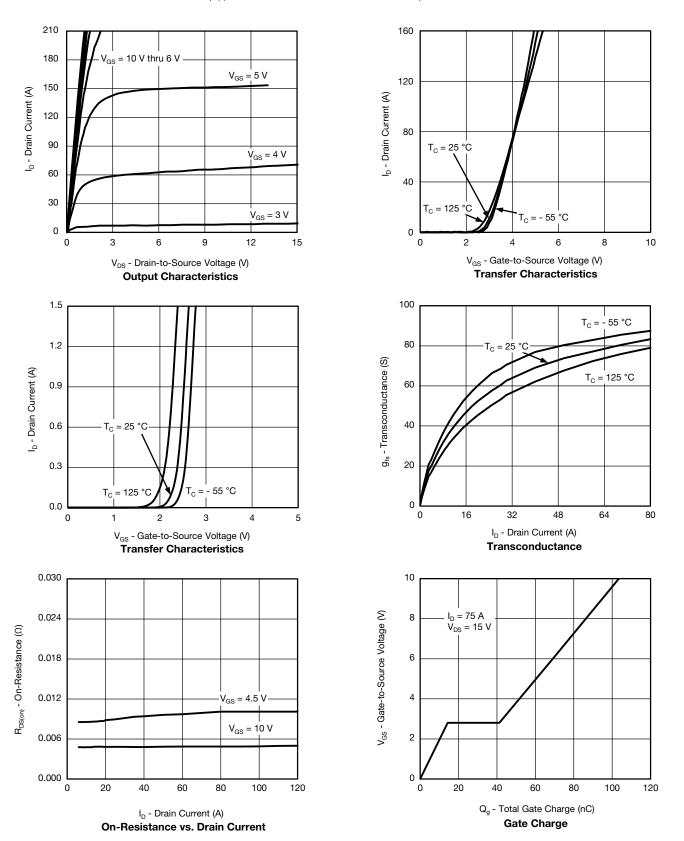
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

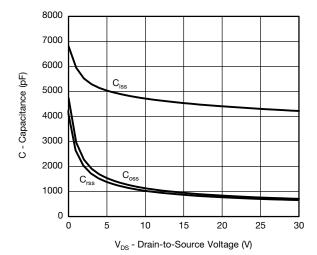


## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

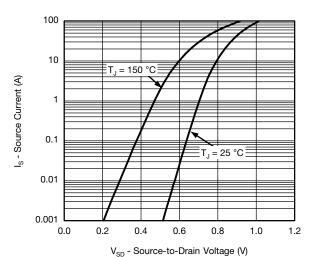




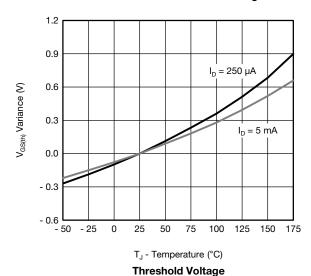
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

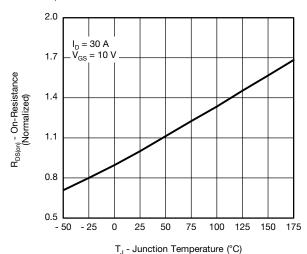


### Capacitance

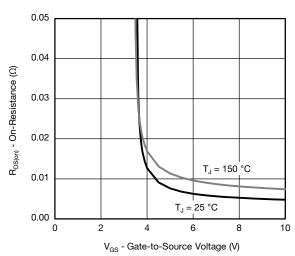


Source Drain Diode Forward Voltage

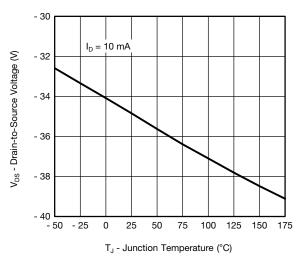




On-Resistance vs. Junction Temperature



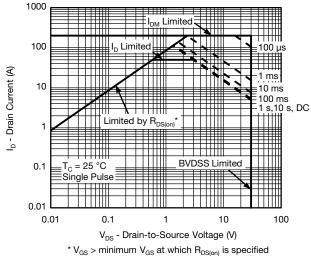
On-Resistance vs. Gate-to-Source Voltage



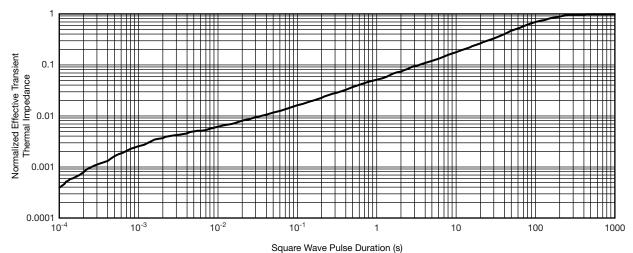
**Drain Source Breakdown vs. Junction Temperature** 



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



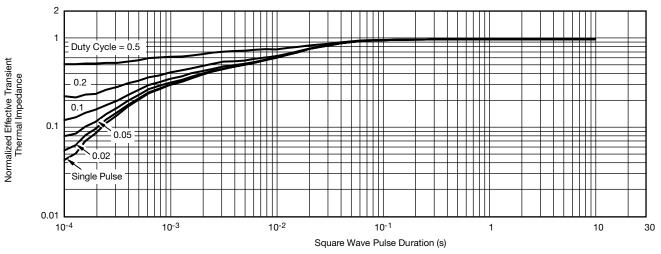
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

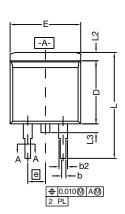
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

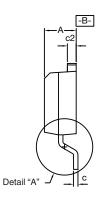
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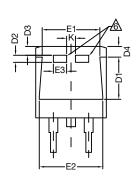


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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

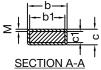








**DETAIL A (ROTATED 90°)** 



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ı	WHITTEN S	1	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INCHES		MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	BSC	2.54 BSC	
	K	0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
	L4	0.010 BSC		0.254 BSC	
	М	-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					

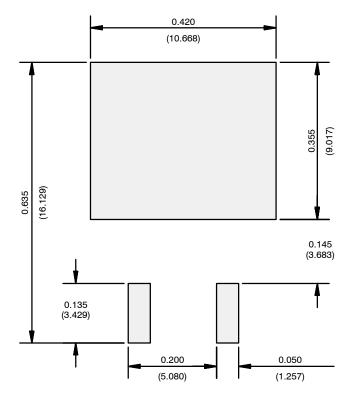
DWG: 5843

Revison: 30-Sep-13 Document Number: 71198





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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